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1.0 Features

- One-chip tunable voltage controlled crystal oscillator (VCXO) allows precise system frequency tuning
- 3.3V operation
- 8 pin SOIC and MSOP packages
- Uses inexpensive 20pF pullable crystals with no external capacitors required.
- 12mA drive capability at TTL levels

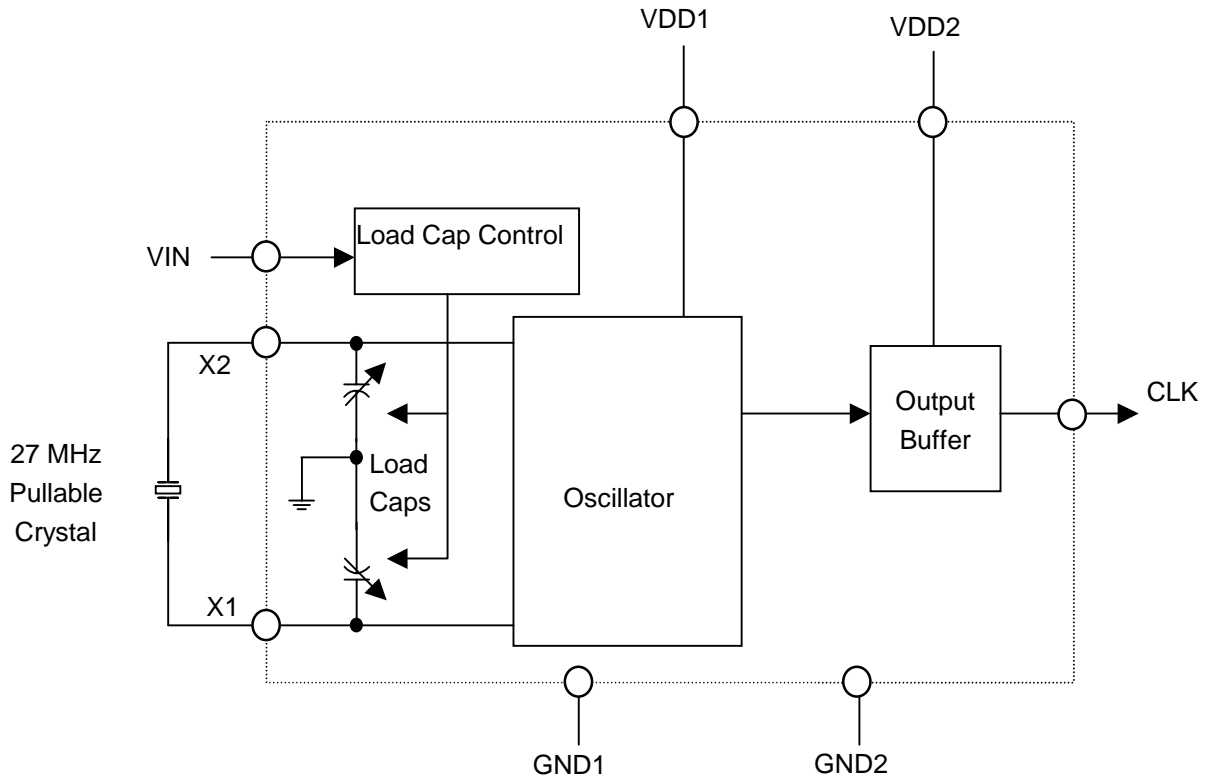
2.0 Applications

- Set-top boxes
- MPEG Video clock source
- Oscillator replacement

3.0 Description

The T73227 is a single-chip, low-jitter Voltage-Controlled-Crystal-Oscillator. The device accepts a 27 MHz, 20 pF crystal, and produces a low jitter output at the same frequency. A 0 to 3.0V control signal is used to fine tune the output clock frequency in the ± 100 ppm range. This finds use in systems that have frequency matching requirements, such as digital satellite receivers.

Figure 1: Block Diagram



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8-pin SOIC/MSOP

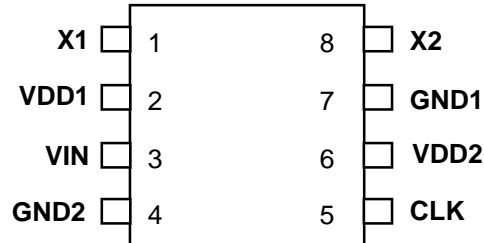


Table 1: Pin Descriptions

PIN	TYPE	NAME	DESCRIPTION
1	Xi	X1	Crystal Connection. Connect to a 27 MHz Pullable Crystal
2	P	VDD1	Core V_{DD} . Connect to 3.3V
3	I	VIN	Voltage input to VCXO. Zero to 3.3V Signal Controls the Frequency of the VCXO.
4	P	GND2	Connect to Ground.
5	O	CLK	Clock Output
6	P	VDD2	Pad Driver V_{DD} . Connect to 3.3V
7	P	GND1	Connect to Ground.
8	Xi	X2	Crystal Connection. Connect to a 27 MHz pullable crystal.

Legend: I = Input

O = Output

P = Power supply connection

Xi = Crystal connections.

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4.0 Functional Block Description

The VCXO provides a tunable, low-jitter frequency reference. Loading capacitance for the crystal is internal to the T73227. No external components (other than the crystal resonator itself) are required for operation of the VCXO.

Tuning of the VCXO frequency is accomplished by varying the voltage on Vin (Pin 3).

The oscillator operates the crystal resonator in the parallel-resonant mode. Crystal warping, or the “pulling” of the crystal oscillation frequency, is accomplished by altering the effective load capacitance presented to the crystal by the oscillator circuit. The actual amount that changing the load capacitance alters the oscillator frequency will be dependent on the characteristics of the crystal as well as the oscillator circuit itself.

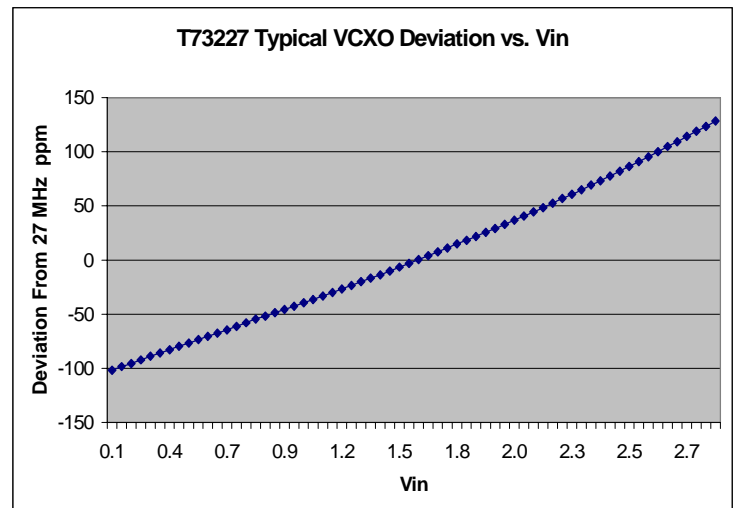
Specifically, the motional capacitance of the crystal (usually referred to by crystal manufacturers as C_1), the static capacitance of the crystal (C_0), and the load capacitance (C_L) of the oscillator determine the “warping” or “pulling” capability of the crystal in the oscillator circuit. A simple formula to obtain the warping capability of a crystal oscillator is:

$$\Delta f (ppm) = \frac{C_1 \times (C_{L2} - C_{L1}) \times 10^6}{2 \times (C_0 + C_{L2}) \times (C_0 + C_{L1})}$$

where C_{L1} and C_{L2} are the two extremes of the applied load capacitance.

EXAMPLE: A crystal with the following parameters is used. With $C_1 = 0.025\text{pF}$, $C_0 = 6\text{pF}$, $C_{L1} = 10\text{pF}$, and $C_{L2} = 20\text{pF}$, the tuning range is

$$\Delta f = \frac{0.025 \times (20 - 10) \times 10^6}{2 \times (6 + 20) \times (6 + 10)} = 300 \text{ ppm}.$$



5.0 Electrical Specifications

Table 2: Absolute Maximum Ratings

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. These conditions represent a stress rating only, and functional operation of the device at these or any other conditions above the operational limits noted in this specification is not implied. Exposure to maximum rating conditions for extended conditions may affect device performance, functionality, and reliability.

PARAMETER	SYMBOL	MIN.	MAX.	UNITS
Supply Voltage ($V_{SS} = \text{ground}$)	V_{DD}	$V_{SS}-0.5$	5	V
Input Voltage, dc	V_I	$V_{SS}-0.5$	$V_{DD}+0.5$	V
Output Voltage, dc	V_O	$V_{SS}-0.5$	$V_{DD}+0.5$	V
Input Clamp Current, dc ($V_I < 0$ or $V_I > V_{DD}$)	I_{IK}	-25	25	mA
Output Clamp Current, dc ($V_I < 0$ or $V_I > V_{DD}$)	I_{OK}	-50	50	mA
Storage Temperature Range (non-condensing)	T_S	-65	150	°C
Ambient Temperature Range, Under Bias	T_A	-55	125	°C
Junction Temperature	T_J		125	°C
Lead Temperature (soldering, 10s)			260	°C
Input Static Discharge Voltage Protection			2	KV

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Table 3: Operating Conditions

PARAMETER	SYMBOL	CONDITIONS/DESCRIPTION	MIN.	TYP.	MAX.	UNITS
Core Supply Voltage (V_{DD})	V_{DD}		3.15	3.3	3.45	V
VCXO Control Voltage, V_{IN}	V_{IN}		0		V_{DD}	V
Ambient Operating Temperature Range	T_A		0		70	°C
Crystal Resonator Frequency	f_{XTAL}	Fundamental Mode	20	27	30	MHz
Crystal Load Capacitance	$C_{L(xtal)}$	AT cut		20		pF

Table 4: DC Electrical Specifications

Unless otherwise stated, $V_{DD} = 3.15V$ to $3.45V$, no load on any output, and ambient temperature range $T_A = 0^\circ C$ to $70^\circ C$.

PARAMETER	SYMBOL	CONDITIONS/DESCRIPTION	MIN.	TYP.	MAX.	UNITS
Overall						
Supply Current, Dynamic, with no load	I_{DD}	$f_{XTAL} = 27MHz$		25		mA
Output High Voltage	V_{OH}	$I_{OH} = -12mA$	2.4			V
Output Low Voltage	V_{OL}	$I_{OL} = 12mA$			0.4	V
Voltage Controlled Crystal Oscillator - $V_{DD}=3.3V$						
Crystal Loading Capacitance	$C_{L(xtal)}$	As seen by a crystal connected to XIN and XOUT (@ $V_{XTUNE} = 1.65V$)		20		pF
Crystal Gamma	C_0/C_1				240	
VCXO Tuning Range		$f_{XTAL} = 27MHz$; $C_{L(xtal)} = 20pF$; $\gamma = 240$		250		ppm
VCXO Tuning Characteristic		Note: positive ΔF for positive ΔV		75		ppm/V
Crystal ESR					50	Ω

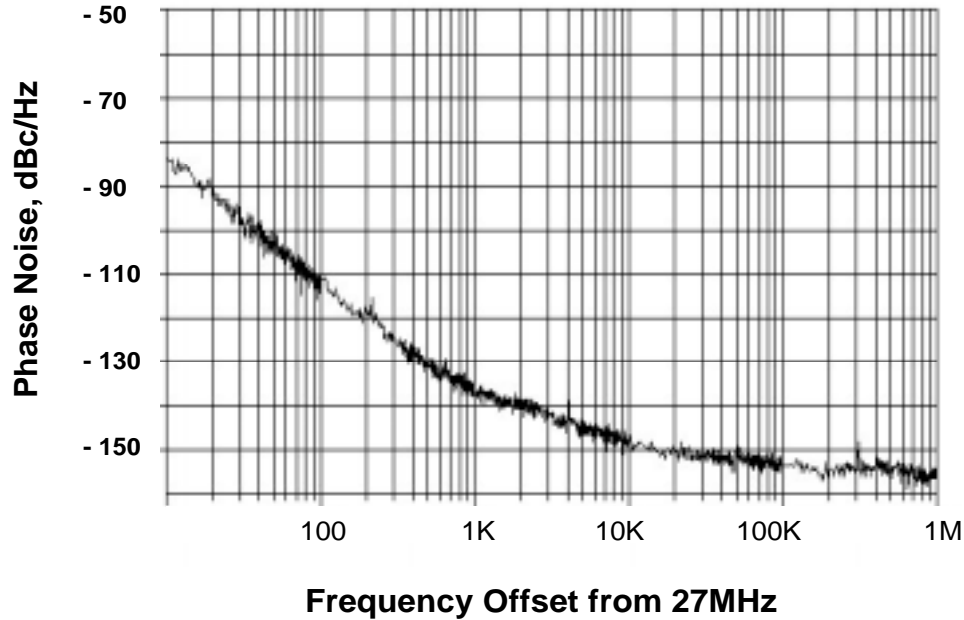
Table 5: AC Timing Specifications

Unless otherwise stated, $V_{DD} = 3.15V$ to $3.45V$, no load on any output, and ambient temperature range $T_A = 0^\circ C$ to $70^\circ C$. Parameters denoted with an asterisk (*) represent nominal characterization data and are not production tested to any specific limits.

PARAMETER	SYMBOL	CONDITIONS/DESCRIPTION	MIN.	TYP.	MAX.	UNITS
Clock Output (CLK)						
Duty Cycle *		Ratio of high pulse width (as measured from rising edge to next falling edge at $V_{DD}/2$) to one clock period	40		60	%
Jitter, Period (peak-peak) *	$t_{j(\Delta P)}$	From rising edge to next rising edge at $V_{DD}/2$, $C_L = 10pF$			150	ps
Rise Time *	t_r	Measured 0.8V to 2.0V, $C_L = 10pF$			1.5	ns
Fall Time *	t_f	Measured 2.0V to 0.8V; $C_L = 10pF$			1.5	ns

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Phase Noise vs. Frequency Offset



6.0 Ordering Information

ORDERING PART NUMBER	PACKAGE TYPE	SHIPPING CONFIGURATION
T73227-S08	8-pin SOIC	Tubes
T73227-S08-TNR	8-pin SOIC	Tape and Reel
T73227-M08	8-pin MSOP	Tubes
T73227-M08-TNR	8-pin MSOP	Tape and Reel
T73227-DIE	DIE	Waffle-Pack

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